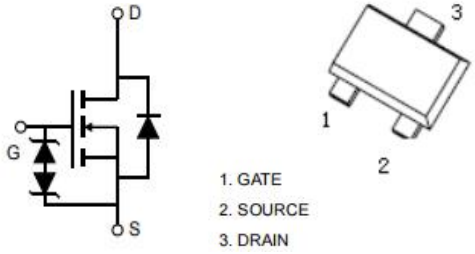
SOT-723 30V N Channel Enhancement ESD Protection 沟道增强型带静电保护
MOS Field Effect Transistor 场效应管



■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	±12	V
Drain Current (continuous)漏极电流-连续	I_D（at T_A = 25°C）	0.7	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	1.8	A
Total Device Dissipation 总耗散功率	P_D(at T_A = 25°C)	150	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\Theta JA}$	850	℃/W
ESD Protected Up to 人体模式静电保护范围	ESD(HBM)	2.0	kV
Junction/Storage Temperature 结温/储存温度	T_J,T_{stg}	-55~150	℃

■Device Marking 产品字标

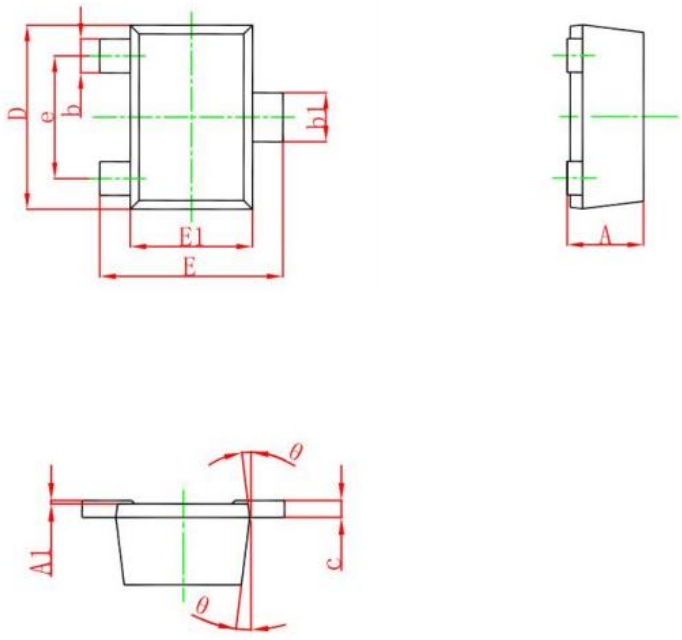
FS3144KT7=KM

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I_D =250uA,V_{GS}=0V)	BV_{DSS}	30	—	—	V
Gate Threshold Voltage 栅极开启电压(I_D =250uA,V_{GS}= V_{DS})	$V_{GS(th)}$	0.6	0.95	1.3	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V_{GS}=0V, V_{DS}= 30V)	I_{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流(V_{GS}=±12V, V_{DS}=0V)	I_{GSS}	—	—	±10	μA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I_D=0.5A,V_{GS}=4.5V) (I_D=0.5A,V_{GS}=2.5V)	$R_{DS(ON)}$	—	350 450	420 560	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I_{SD}=0.7A,V_{GS}=0V)	V_{SD}	—	—	1	V

■Dimension 外形封装尺寸



Symbol	Dimensions In Millimet	
	Min	Max
A	0.40	0.50
A1	0.00	0.10
b	0.15	0.25
b1	0.20	0.30
c	0.06	0.16
D	1.10	1.30
e	0.8TYP	
E	1.10	1.30
E1	0.70	0.90
θ	8°	10°